



7N65K-MTQ

Power MOSFET

7A, 650V N-CHANNEL POWER MOSFET

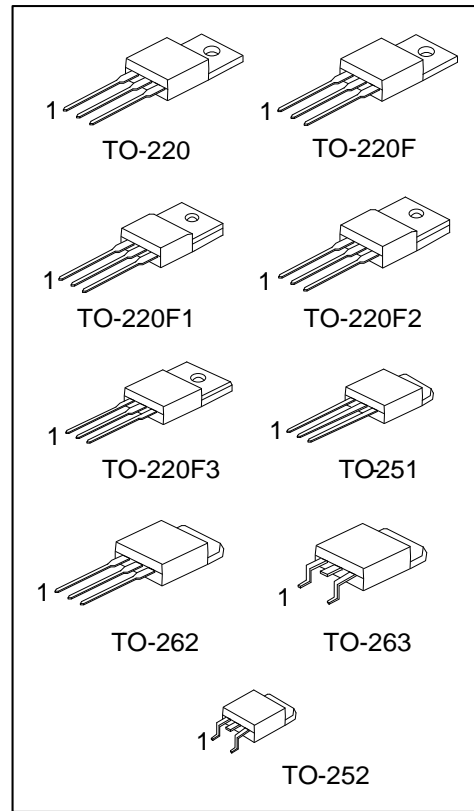
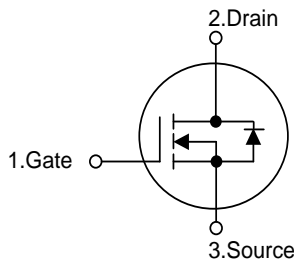
DESCRIPTION

The UTC 7N65K-MTQ is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} \leq 1.6 \Omega @ V_{GS}=10V, I_D=3.5A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL



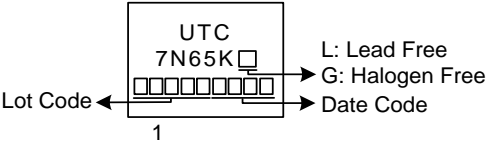
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N65KL-TA3-T	7N65KG-TA3-T	TO-220	G	D	S	Tube
7N65KL-TF3-T	7N65KG-TF3-T	TO-220F	G	D	S	Tube
7N65KL-TF1-T	7N65KG-TF1-T	TO-220F1	G	D	S	Tube
7N65KL-TF2-T	7N65KG-TF2-T	TO-220F2	G	D	S	Tube
7N65KL-TF3T-T	7N65KG-TF3T-T	TO-220F3	G	D	S	Tube
7N65KL-TM3-T	7N65KG-TM3-T	TO-251	G	D	S	Tube
7N65KL-TN3-R	7N65KG-TN3-R	TO-252	G	D	S	Tape Reel
7N65KL-T2Q-T	7N65KG-T2Q-T	TO-262	G	D	S	Tube
7N65KL-TQ2-T	7N65KG-TQ2-T	TO-263	G	D	S	Tube
7N65KL-TQ2-R	7N65KG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>7N65KG-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220F, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TN3: TO-252, T2Q: TO-262, TQ3: TO-263</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	650	V
Gate-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current		I _D	7	A
Pulsed Drain Current (Note 2)		I _{DM}	24	A
Avalanche Current (Note 2)		I _{AR}	7	A
Avalanche Energy, Repetitive, Limited by T _{JMAX}		E _{AR}	2	mJ
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	350	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P _D	125	W
	TO-220F/TO-220F1 TO-220F2/TO-220F3		38	W
	TO-251/TO-252		55	W
Junction Temperature		T _J	+150	°C
Operating Temperature		T _{OPR}	-55 ~ +150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 14.28mH, I_{AS} = 7A, V_{DD} = 90V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 7A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3/TO-262 TO-263	θ _{JA}	62.5	°C/W
	TO-251/TO-252		110	
Junction to Case	TO-220/TO-262 TO-263	θ _{JC}	1.0	°C/W
	TO-220F/TO-220F1 TO-220F2/TO-220F3		3.29	
	TO-251/TO-252		2.27 (Note)	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

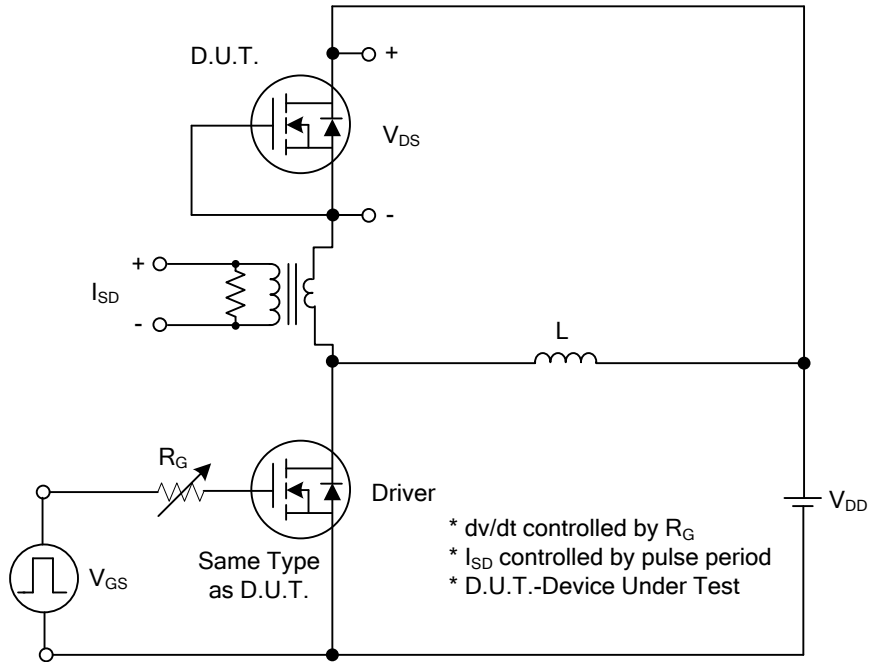
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, Referenced to 25°C		0.53		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.5A$			1.6	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{ MHz}$		980		pF
Output Capacitance	C_{OSS}			90		pF
Reverse Transfer Capacitance	C_{RSS}			5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS}=200V, I_D=7.0A, V_{GS}=10V$ $I_G=3mA$ (Note 1, 2)		24.1		nC
Gate-Source Charge	Q_{GS}			7.2		nC
Gate-Drain Charge	Q_{GD}			6		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D = 0.5A, V_{GS}=10V$ $R_G = 25\Omega$ (Note 1, 2)		50		ns
Turn-On Rise Time	t_R			65		ns
Turn-Off Delay Time	$t_{D(OFF)}$			110		ns
Turn-Off Fall Time	t_F			55		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				7	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				28	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 7A$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=7A, di/dt=100A/\mu s$		320		ns
Body Diode Reverse Recovery Charge	Q_{rr}				2.4	

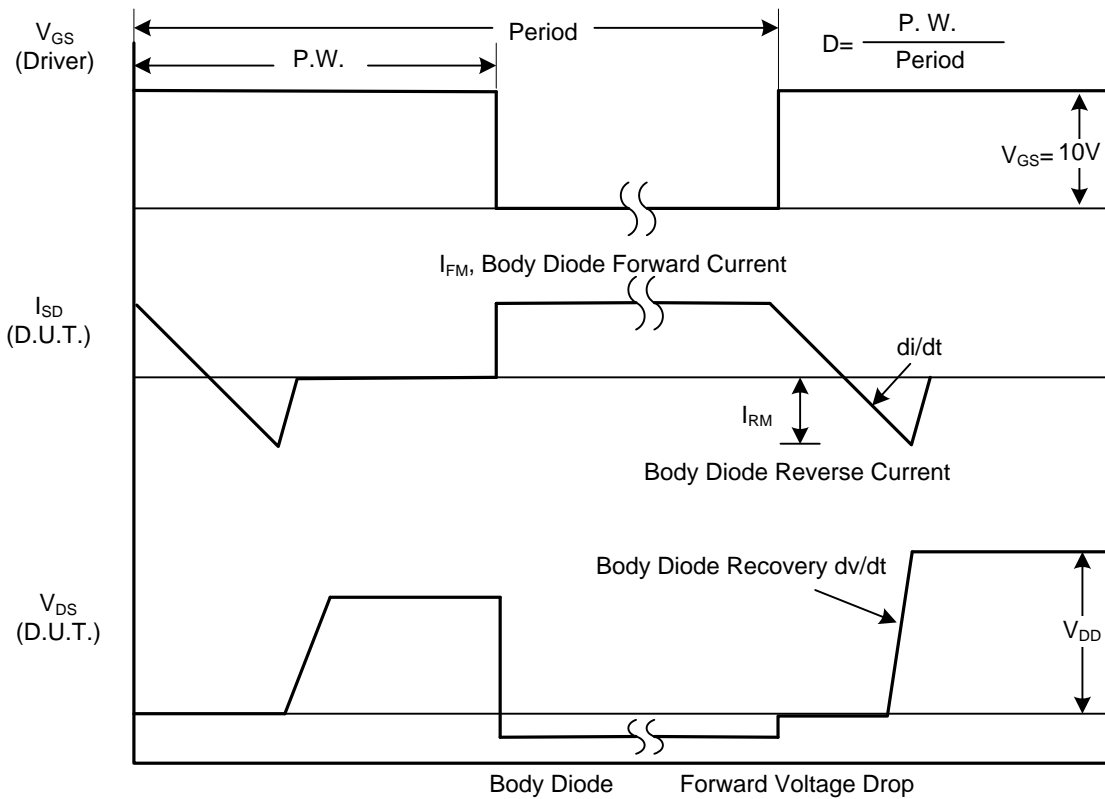
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

TEST CIRCUITS AND WAVEFORMS

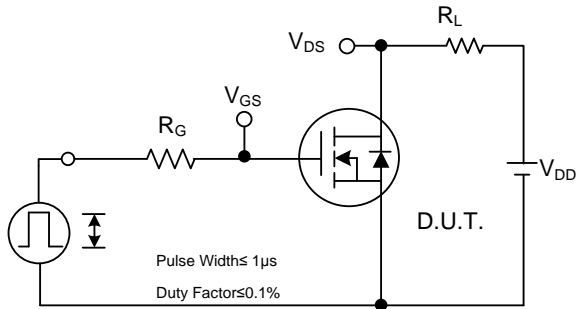


Peak Diode Recovery dv/dt Test Circuit

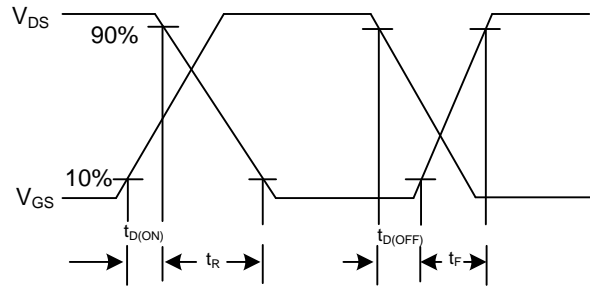


Peak Diode Recovery dv/dt Waveforms

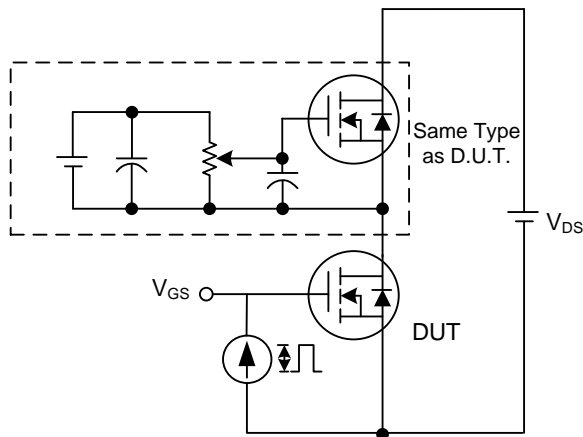
TEST CIRCUITS AND WAVEFORMS



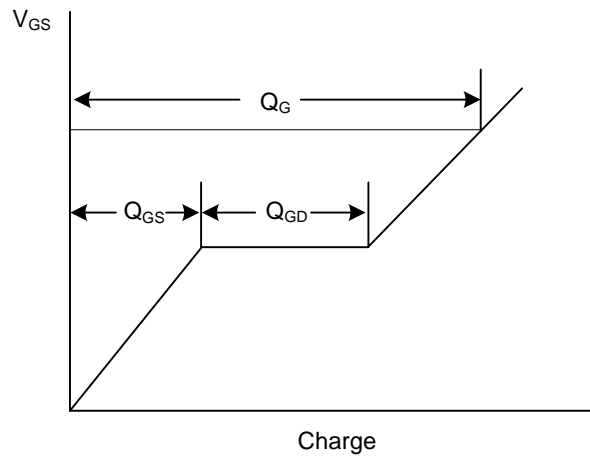
Switching Test Circuit



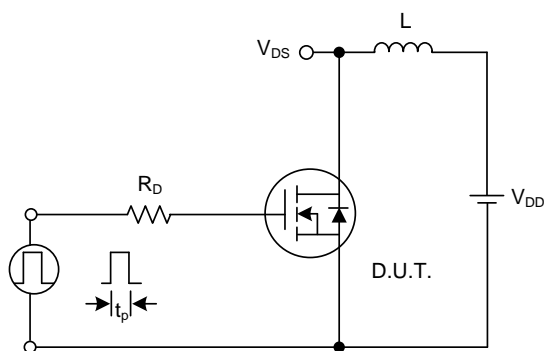
Switching Waveforms



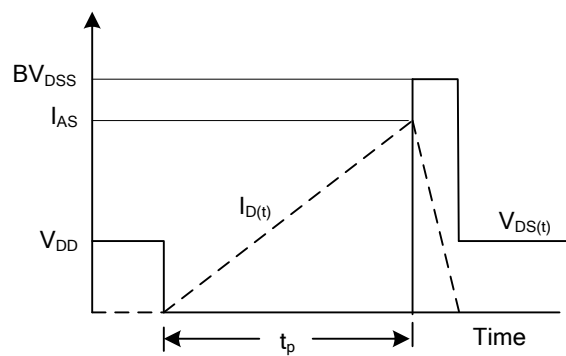
Gate Charge Test Circuit



Gate Charge Waveform

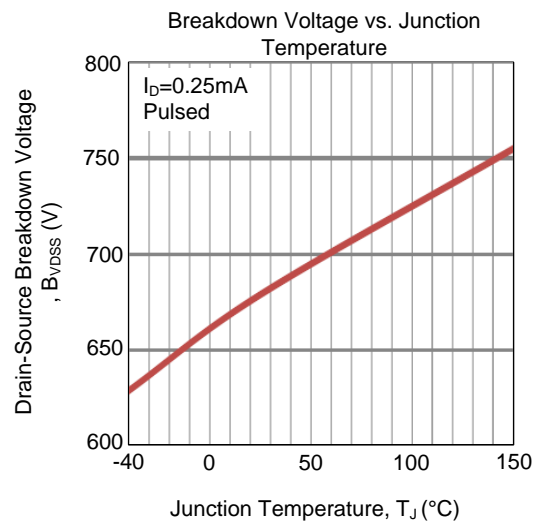
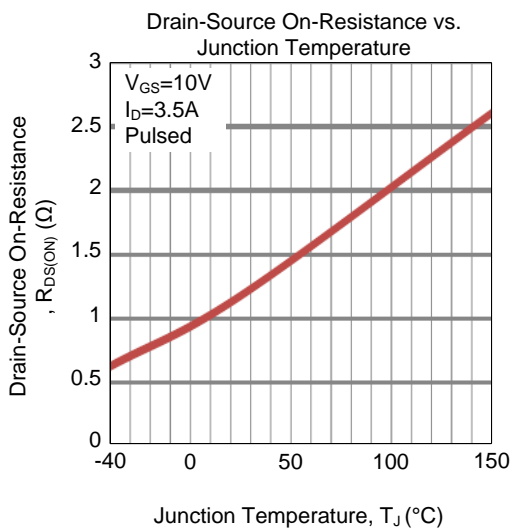
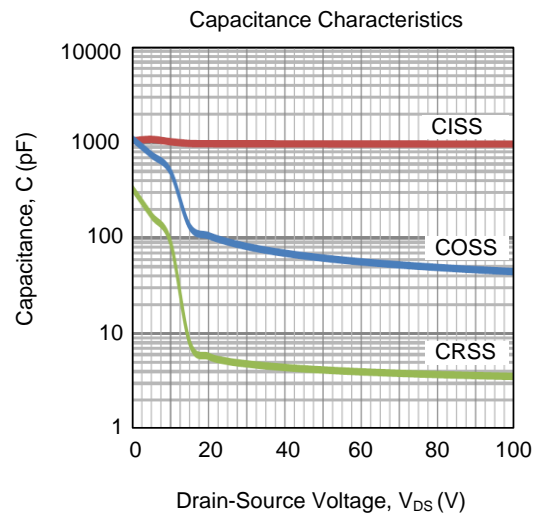
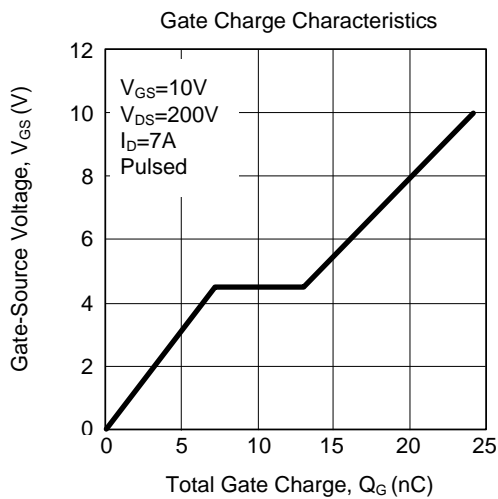
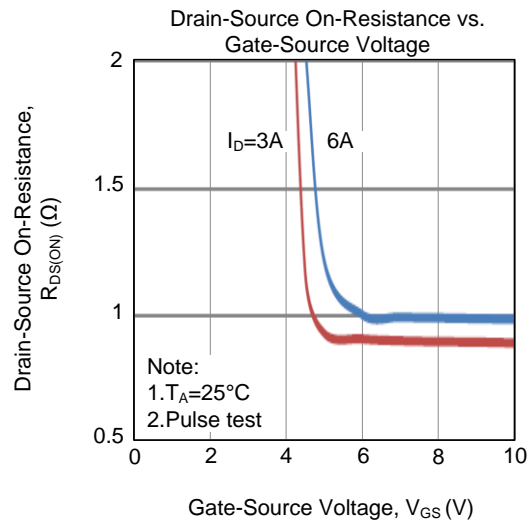
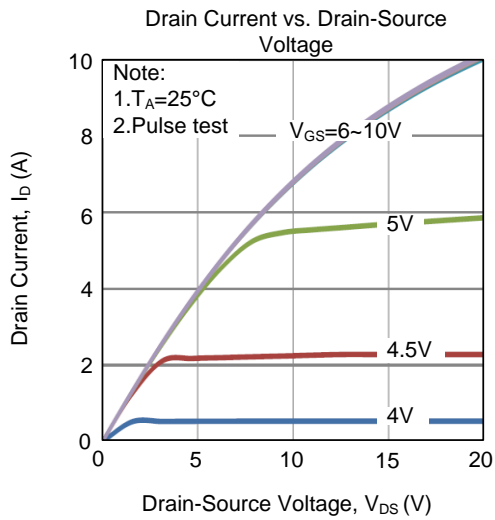


Unclamped Inductive Switching Test Circuit

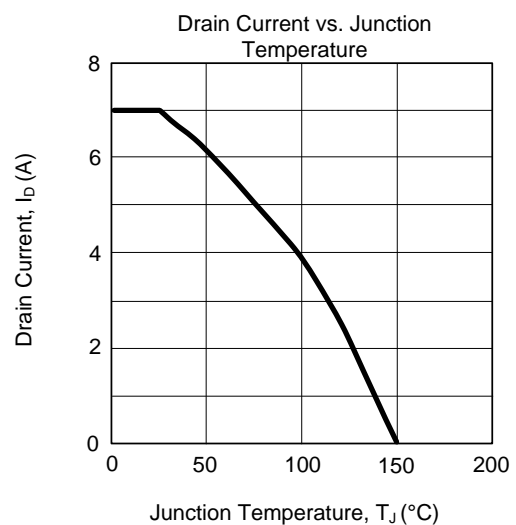
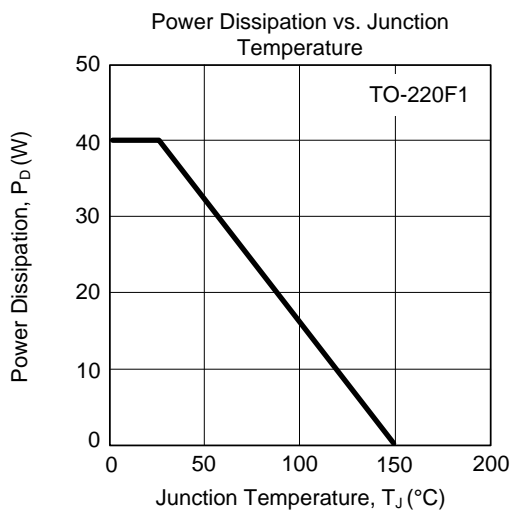
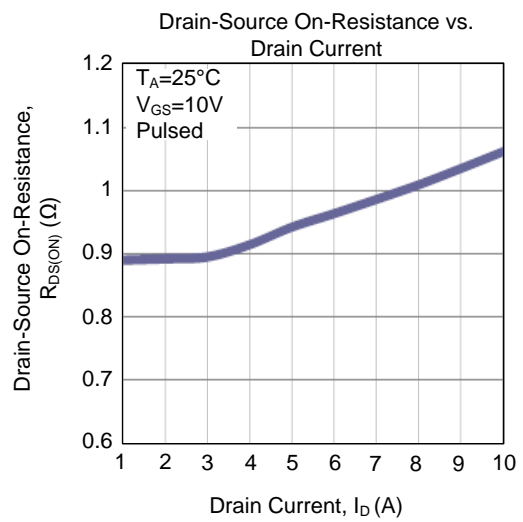
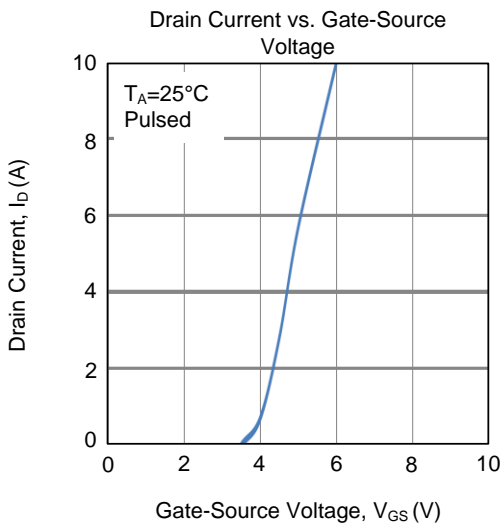
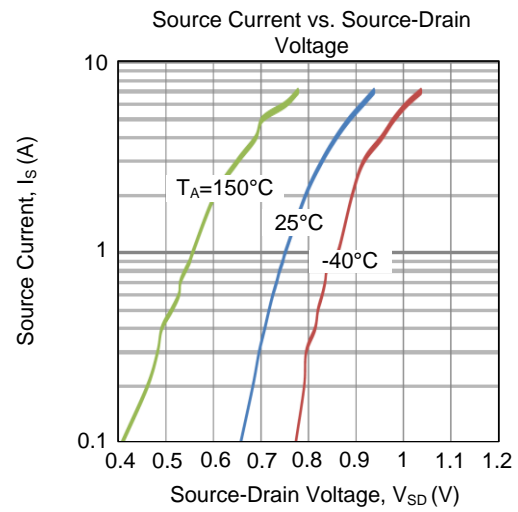
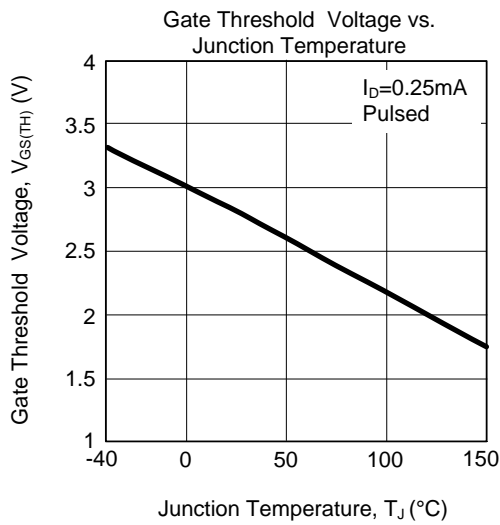


Unclamped Inductive Switching Waveforms

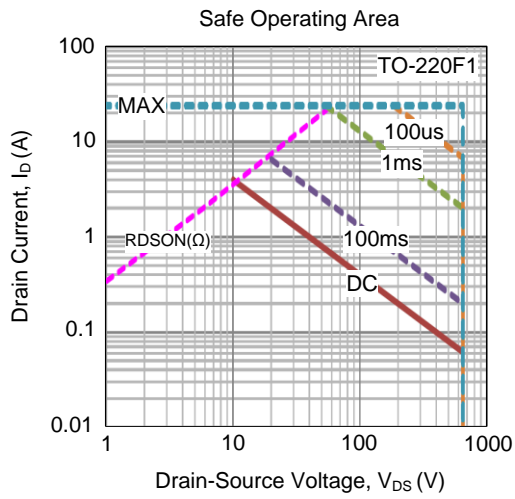
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ **TYPICAL CHARACTERISTICS (Cont.)**



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